

BYW27-50 - BYW27-1000 SILICON RECTIFIERS

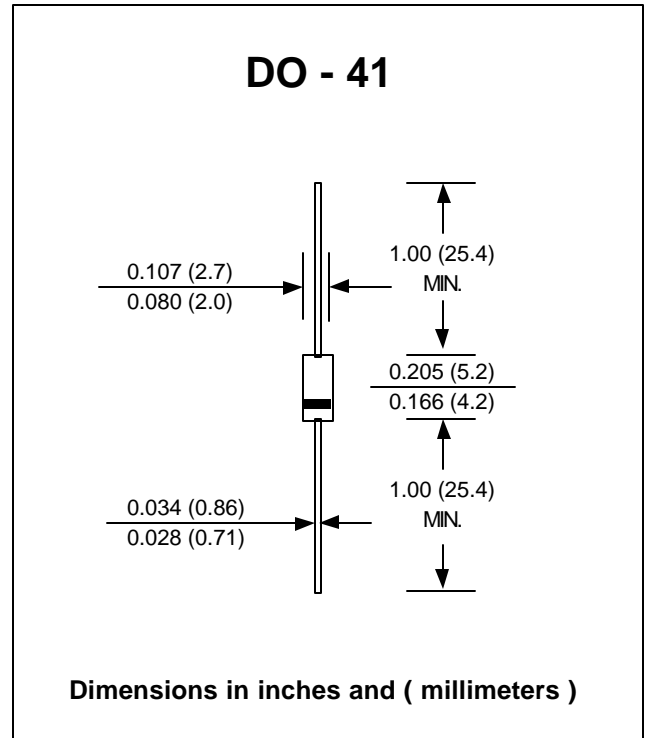
PRV : 50 - 1000 Volts
Io : 1.0 Amperes

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop

MECHANICAL DATA :

- * Case : DO-41 Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.339 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	BYW 27-50	BYW 27-100	BYW 27-200	BYW 27-400	BYW 27-600	BYW 27-800	BYW 27-1000	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Current 0.375" (9.5mm) Lead Length $T_a = 70^\circ\text{C}$	I_F	1.0							Amp.
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	50							Amps.
Maximum Forward Voltage at $I_F = 1.0$ Amp.	V_F	1.0							Volts
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at rated DC Blocking Voltage $T_a = 100^\circ\text{C}$	I_R	0.2							μA
	$I_{R(H)}$	25							μA
Typical Junction Capacitance (Note1)	C_J	30							pF
Typical Thermal Resistance (Note2)	$R_{\theta JA}$	50							$^\circ\text{C/W}$
Junction Temperature Range	T_J	- 65 to + 175							$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 65 to + 175							$^\circ\text{C}$

Notes :

- (1) Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- (2) Thermal resistance from Junction to Ambient at 0.375" (9.5mm) Lead Lengths, P.C. Board Mounted.

RATING AND CHARACTERISTIC CURVES (BYW27-50 - BYW27-1000)

